

# Silicon PNP Transistor

## **MJ2955**

Power Linear and Switching

60V / 15A

# DATASHEET

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OEM –SGS Ates

Source: SGS Ates Databook 1977

**MJ 2955****EPITAXIAL-BASE PNP****POWER LINEAR AND SWITCHING APPLICATIONS**

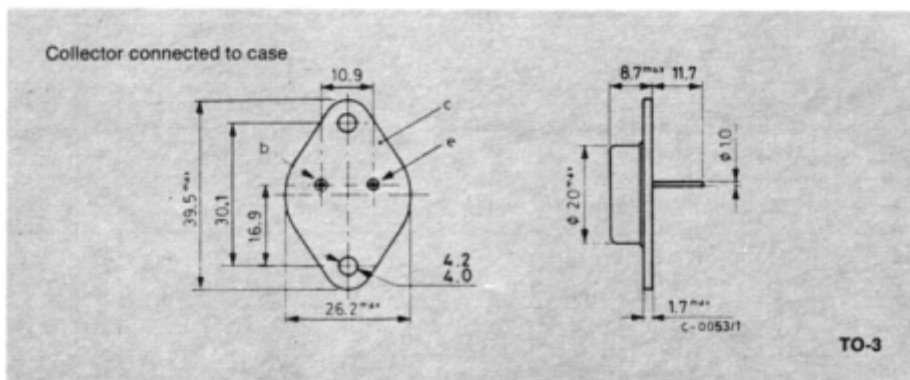
The MJ 2955 is a silicon epitaxial-base PNP power transistor in Jedec TO-3 metal case. It is intended for power switching circuits, series and shunt regulators, output stages and hi-fi amplifiers.

**ABSOLUTE MAXIMUM RATINGS**

$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	-100	V
$V_{CER}$	Collector-emitter voltage ( $R_{BE} \leq 100 \Omega$ )	-70	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	-60	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	-7	V
$I_C$	Collector current	-15	A
$I_B$	Base current	-7	A
$P_{tot}$	Total power dissipation at $T_{case} \leq 25 \text{ }^\circ\text{C}$	150	W
$T_{stg}$	Storage temperature	-65 to 200	$^\circ\text{C}$
$T_j$	Junction temperature	200	$^\circ\text{C}$

**MECHANICAL DATA**

Dimensions in mm



# MJ 2955

## THERMAL DATA

$R_{th\ j-case}$	Thermal resistance junction-case	max	1.17	°C/W
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## ELECTRICAL CHARACTERISTICS ( $T_{case} = 25\text{ °C}$ unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{CEX}$	Collector cutoff current ( $V_{BE} = 1.5V$ )	$V_{CE} = -100V$ $V_{CE} = -100V$		-1 -5	mA mA
$I_{CEO}$	Collector cutoff current ( $I_B = 0$ )	$V_{CE} = -30 V$		-0.7	mA
$I_{EBO}$	Emitter cutoff current ( $I_C = 0$ )	$V_{BE} = 7 V$		-5	mA
$V_{CER(sus)}$ *	Collector-emitter sustaining voltage ( $R_{BE} = 100\ \Omega$ )	$I_C = -200mA$		-70	V
$V_{CEO(sus)}$ *	Collector-emitter sustaining voltage ( $I_B = 0$ )	$I_C = -200mA$		-60	V
$V_{CE(sat)}$ *	Collector-emitter saturation voltage	$I_C = -4 A$ $I_B = -0.4A$ $I_C = -10 A$ $I_B = -3.3A$		-1.1 -3	V V
$V_{BE}$ *	Base-emitter voltage	$I_C = -4 A$ $V_{CE} = -4 V$		-1.8	V
$h_{FE}$ *	DC current gain	$I_C = -4 A$ $V_{CE} = -4 V$ $I_C = -10 A$ $V_{CE} = -4 V$	20 5	70	— —
$f_T$	Transition frequency	$I_C = -0.5A$ $V_{CE} = -10V$	4		MHz

\* Pulsed: pulse duration = 300  $\mu s$ , duty cycle = 1.5%  
For characteristic curves see the 2N 5875 series